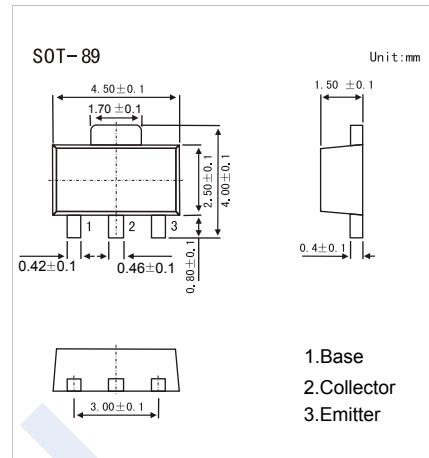


NPN Transistors**2SC2880-HF****■ Features**

- High Voltage: $V_{CEO}=150V$
- High Transition Frequency
- Small Flat Package
- Complementary to 2SA1200-HF
- Pb-Free Package May be Available. The G-Suffix Denotes a Pb-Free Lead Finish

**■ Absolute Maximum Ratings $T_a = 25^\circ C$**

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	200	V
Collector - Emitter Voltage	V_{CEO}	150	
Emitter - Base Voltage	V_{EBO}	5	
Collector Current - Continuous	I_C	50	mA
Base Current	I_B	10	
Collector Power Dissipation (Note.1)	P_C	500	mW
		800	
Junction Temperature	T_J	150	°C
Storage Temperature Range	T_{stg}	-55 to 150	

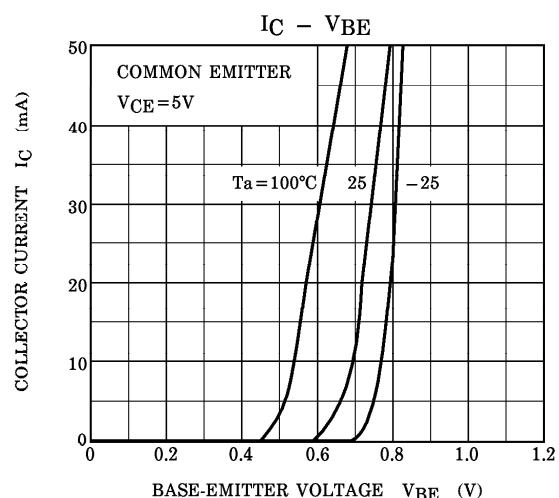
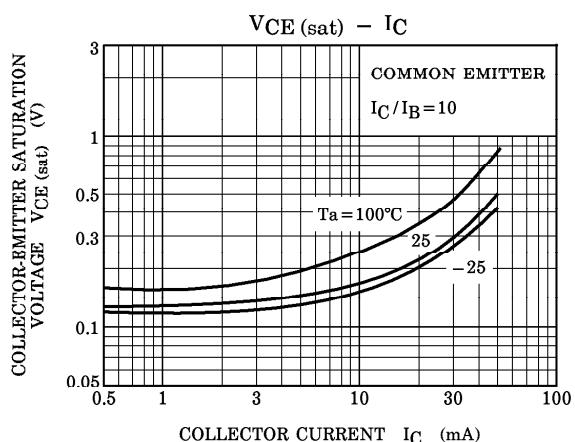
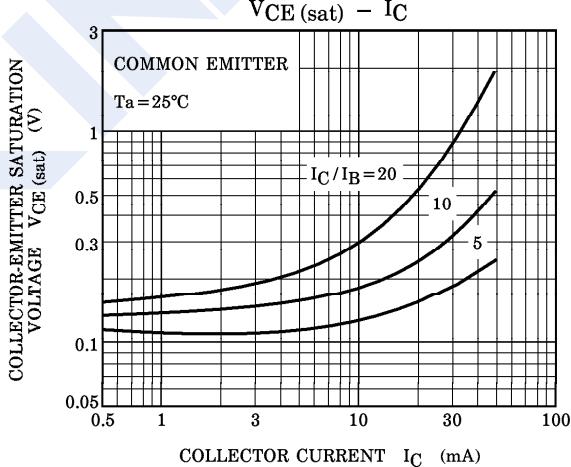
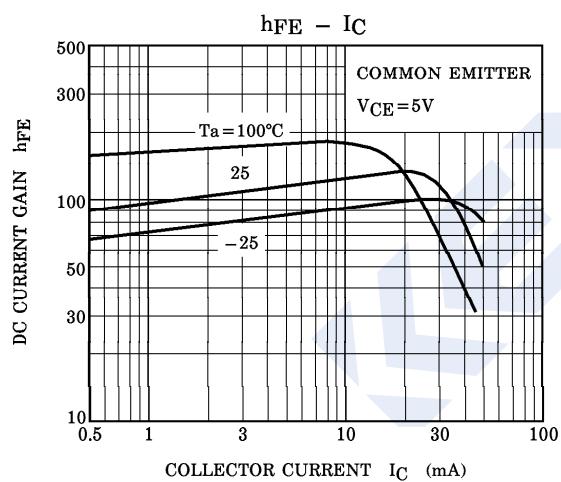
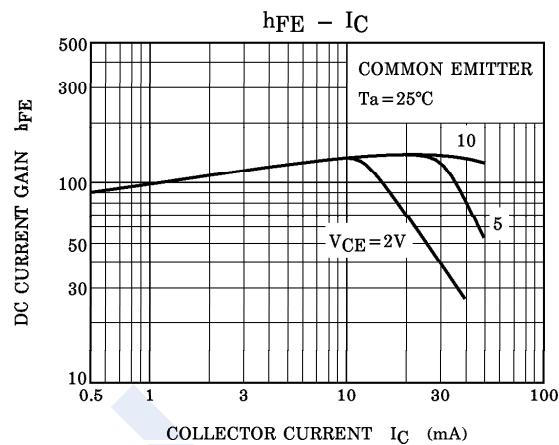
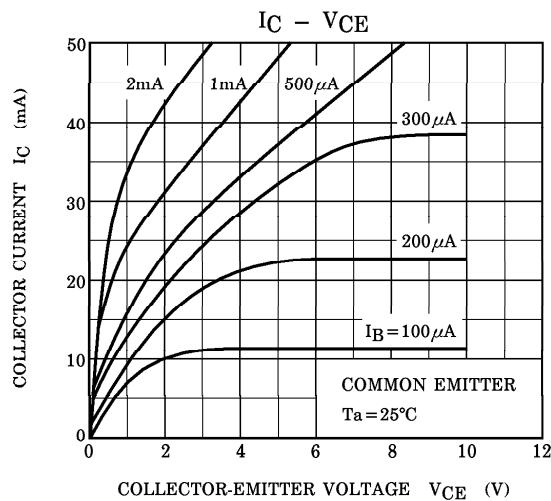
Note.1: Mounted on ceramic substrate(250mm²X0.8t)

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V_{CBO}	$I_C= 100 \mu A, I_E= 0$	200			V
Collector-emitter breakdown voltage	V_{CEO}	$I_C= 1 mA, I_B= 0$	150			
Emitter-base breakdown voltage	V_{EBO}	$I_E= 100 \mu A, I_C= 0$	5			
Collector-base cut-off current	I_{CBO}	$V_{CB}= 200V, I_E= 0$		0.1		uA
Emitter cut-off current	I_{EBO}	$V_{EB}= 5V, I_C= 0$		0.1		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C= 10 mA, I_B= 1mA$		0.5		V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C= 10 mA, I_B= 1mA$		1.2		
Base-emitter voltage	V_{BE}	$V_{CE}= 5V, I_C= 30mA$		1		
DC current gain	h_{FE}	$V_{CE}= 5V, I_C= 10mA$	70		240	
Collector output capacitance	C_{ob}	$V_{CB}= 10V, I_E= 0, f= 1MHz$		3.5	5	pF
Transition frequency	f_T	$V_{CE}= 30V, I_C= 10mA$		120		MHz

■ Classification of hfe

Type	2SC2880-O-HF	2SC2880-Y-HF
Range	70-140	120-240
Marking	AO _F	AY _F

NPN Transistors**2SC2880-HF****■ Typical Characteristics**

NPN Transistors**2SC2880-HF****■ Typical Characteristics**